

Description

The SX20P03DF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -30V$ $I_D = 28A$

$R_{DS(ON)} < 20m\Omega$ @ $V_{GS}=10V$

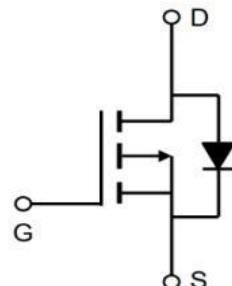
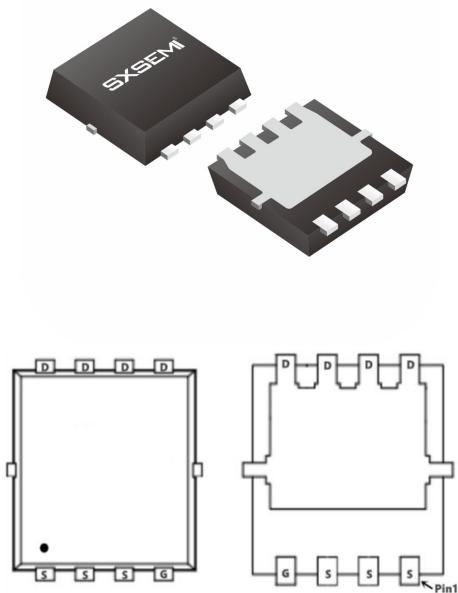
Application

Lithium battery protection

Wireless impact

Mobile phone fast charging

PDFN3*3-8L



Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-30	V
VGS	Gate-Source Voltage	± 20	V
ID@TC=25°C	Continuous Drain Current, VGS @ -10V1	-28	A
ID@TC=100°C	Continuous Drain Current, VGS @ -10V1	-16	A
IDM	Pulsed Drain Current2	-80	A
EAS	Single Pulse Avalanche Energy3	16	mJ
IAS	Avalanche Current	-17	A
PD@TC=25°C	Total Power Dissipation4	16.6	W
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
R _{θJA}	Thermal Resistance Junction-Ambient 1	85	°C/W
R _{θJC}	Thermal Resistance Junction-Case1	3.6	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=-250\mu\text{A}$	-30	-33	-	V
IDSS	Zero Gate Voltage Drain Current	$V_{DS}=-30\text{V}$, $V_{GS}=0\text{V}$,	-	-	-1	μA
IGSS	Gate to Body Leakage Current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$	-	-	± 100	nA
VGS(th)	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-1.2	-1.5	-2.5	V
RDS(on)	Static Drain-Source on-Resistance note3	$V_{GS}=-10\text{V}$, $I_D=-10\text{A}$	-	16.5	20	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$, $I_D=-5\text{A}$	-	23	30	
Ciss	Input Capacitance	$V_{DS}=-15\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$	-	1250	-	pF
Coss	Output Capacitance		-	327	-	pF
Crss	Reverse Transfer Capacitance		-	278	-	pF
Qg	Total Gate Charge	$V_{DS}=-15\text{V}$, $I_D=-9.1\text{A}$, $V_{GS}=-10\text{V}$	-	30	-	nC
Qgs	Gate-Source Charge		-	5.3	-	nC
Qgd	Gate-Drain("Miller") Charge		-	7.6	-	nC
td(on)	Turn-on Delay Time	$V_{DD}=-15\text{V}$, $I_D=-6\text{A}$, $V_{GS}=-10\text{V}$, $R_{GEN}=2.5\Omega$	-	14	-	ns
tr	Turn-on Rise Time		-	20	-	ns
td(off)	Turn-off Delay Time		-	95	-	ns
tf	Turn-off Fall Time		-	65	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	-10	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-40	A
VSD	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}$, $I_S=-11\text{A}$	-	-0.8	-1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3、The EAS data shows Max. rating . The test condition is $VDD=-25\text{V}$, $VGS=-10\text{V}$, $L=0.1\text{mH}$, $IAS=-23\text{A}$
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

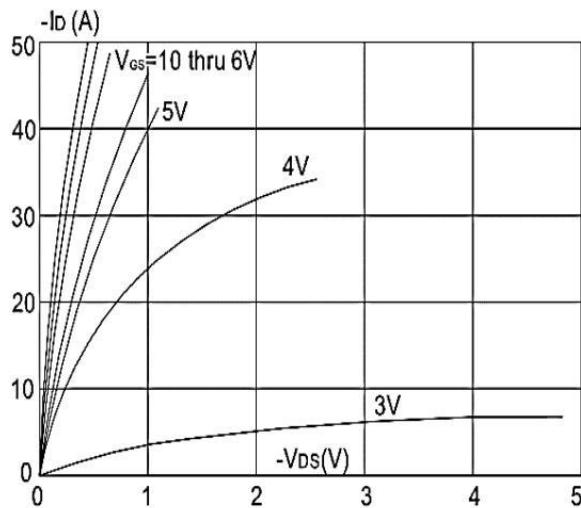


Figure 1: Output Characteristics

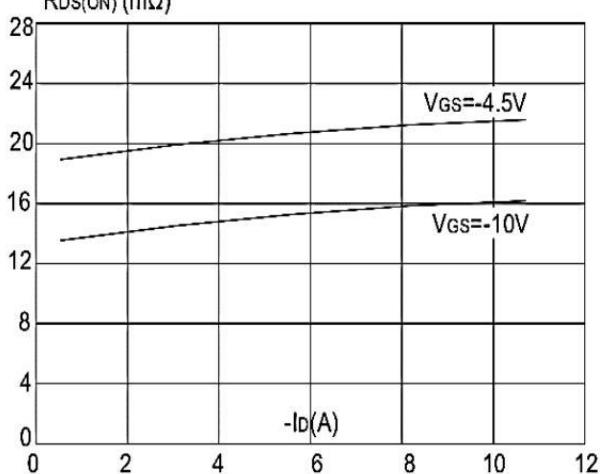


Figure 3: On-resistance vs. Drain Current

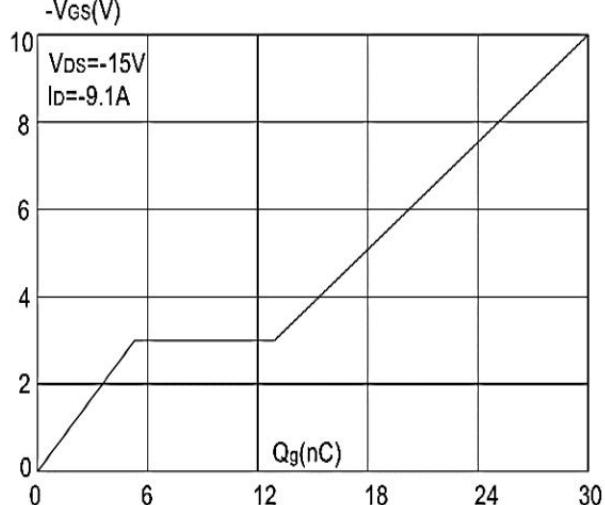


Figure 5: Gate Charge Characteristics

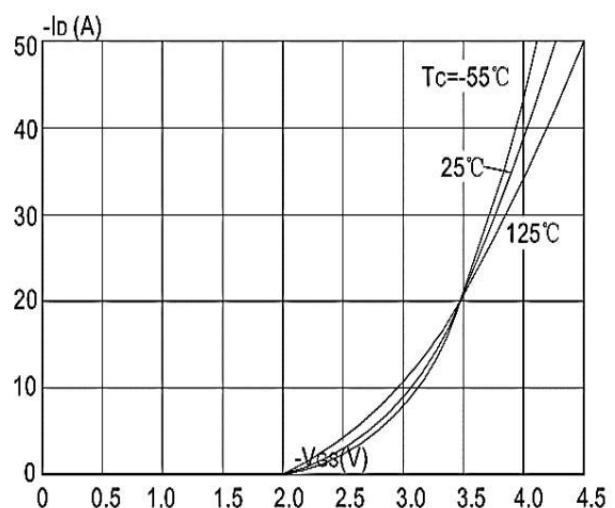


Figure 2: Typical Transfer Characteristics

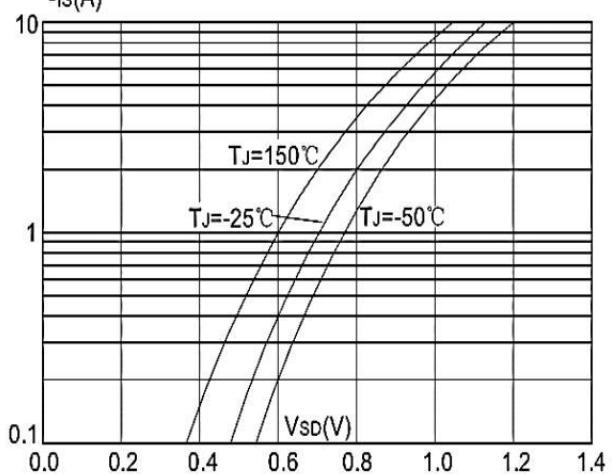


Figure 4: Body Diode Characteristics

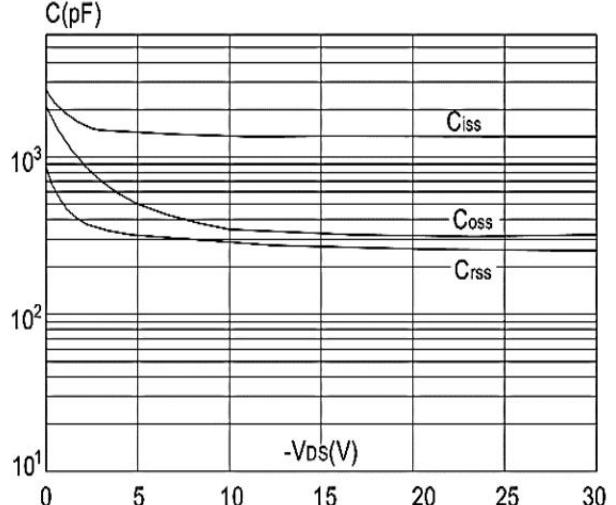


Figure 6: Capacitance Characteristics

Typical Characteristics

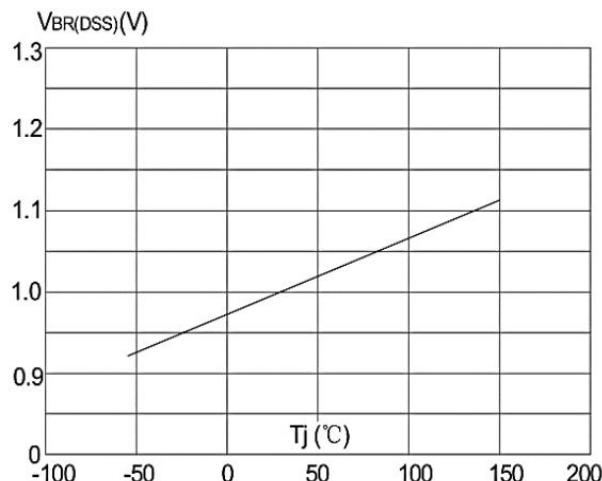


Figure 7: Normalized Breakdown Voltage vs.
Junction Temperature

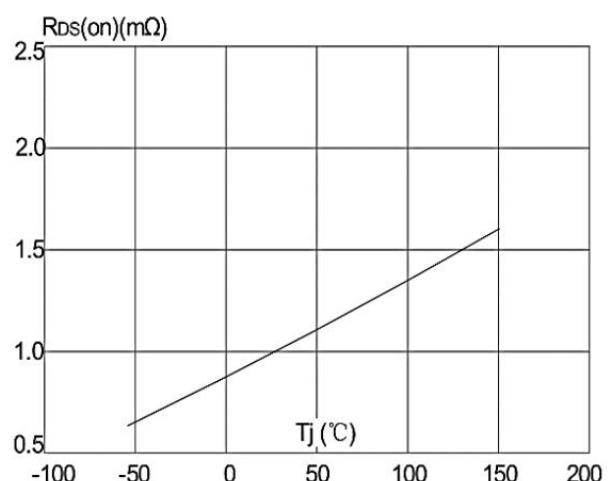


Figure 8: Normalized on Resistance vs.
Junction Temperature

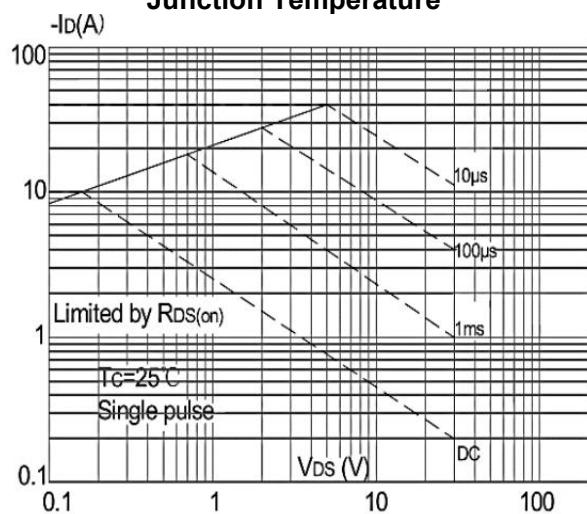


Figure 9: Maximum Safe Operating Area

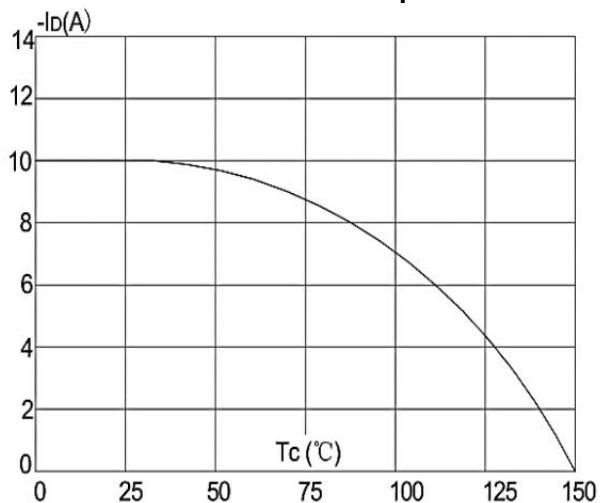


Figure 10: Maximum Continuous Drain Current
vs. Ambient Temperature

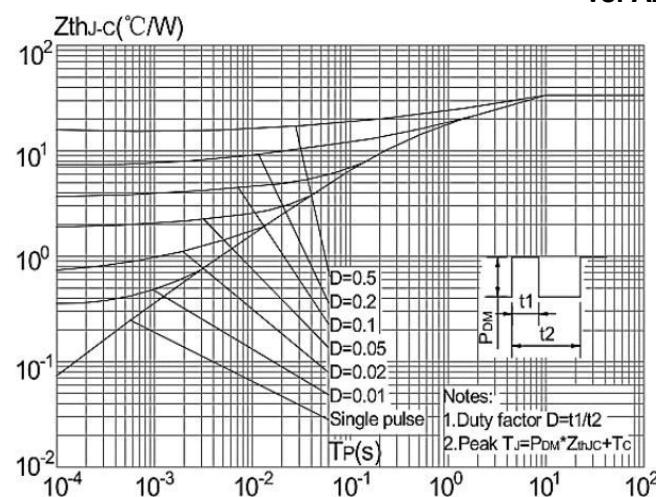
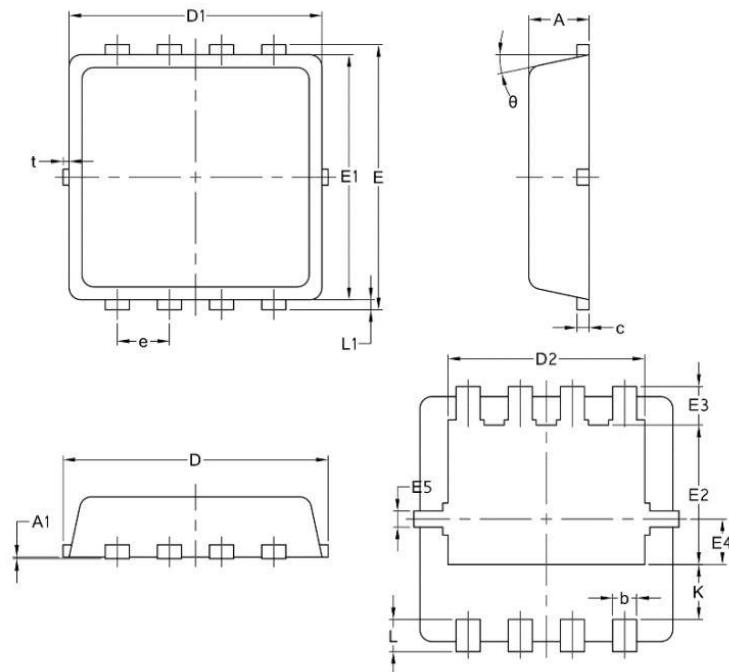


Figure 11: Maximum Effective
Transient Thermal Impedance, Junction-to-Ambient

Package Mechanical Data-PDFN3*3-8L-JQ Single



Symbol	Common		
	mm		
	Mim	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
Φ	10	12	14

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN3*3-8L		5000